Description

The AR1221D3 is an bi-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high-speed data lines. The AR1221D3 has an ultra-low capacitance with a typical value at 0.3pF, and complies with the IEC 61000-4-2 (ESD) with ±20kV air and ±20kV contact discharge. The small size, ultra-low capacitance and high ESD surge protection make AR1221D3 an ideal choice to protect cell phone, digital visual interfaces, HDMI, DVI, USB2.0, USB3.0, and other high speed ports.

Features

- Ultra low capacitance: 0.3pF typical
- Ultra low leakage: nA level
- Operating voltage: 12V
- Low clamping voltage
- 2-Pin leadless package
- Complies with following standards:
  - IEC 61000-4-2 (ESD) immunity test
    - Air discharge: ±20kV
    - Contact discharge: ±20kV
  - IEC61000-4-5 (Lightning) 2A (8/20μs)
- RoHS Compliant

Mechanical Characteristics

- Package: SOD-323
- Case Material: “Green” Molding Compound.
- Terminal Connections: See Diagram Below
- Marking Information: See Below

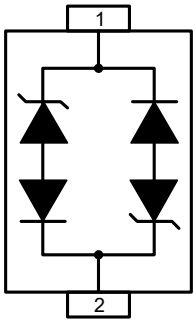
Applications

- Cellular Handsets and Accessories
- Display Ports
- MDDI Ports
- USB Ports
- Digital Visual Interface (DVI)
- PCI Express and Serial SATA Ports
- Capacity Pens for Touchscreen Laptop

Marking Information

12D = Device Marking Code

Equivalent Circuit and Pin Configuration



Circuit and Pin Schematic

Ordering Information

Part Number	Packaging	Reel Size
AR1221D3	3000/Tape & Reel	7 inch

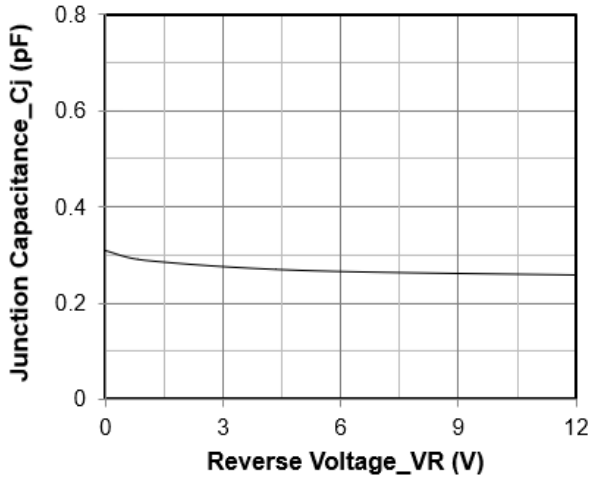
Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20μs)	Ppk	60	W
Peak Pulse Current (8/20μs)	I_{PP}	2	A
ESD per IEC 61000−4−2 (Air) ESD per IEC 61000−4−2 (Contact)	V_{ESD}	±20 ±20	kV
Operating Temperature Range	T_J	−55 to +125	°C
Storage Temperature Range	Tstg	−55 to +150	°C

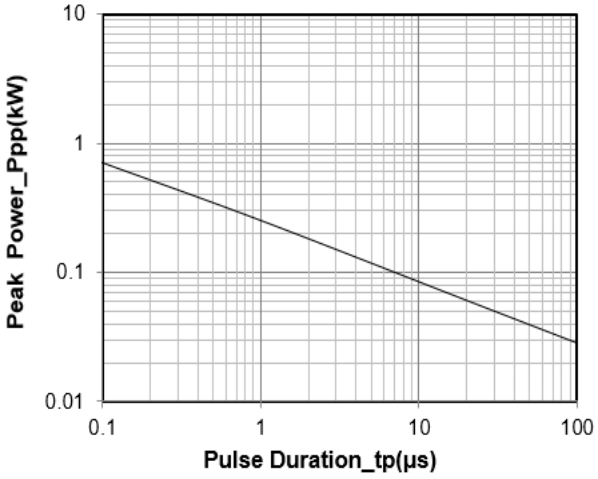
Electrical Characteristics (T_A=25°C unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V_{RWM}			12	V	
Breakdown Voltage	V_{BR}	13.3			V	I_T = 1mA
Reverse Leakage Current	I_R			0.2	μA	V_{RWM} = 12V
Clamping Voltage	V_C			30	V	I_{PP} = 2A (8 x 20μs pulse)
Junction Capacitance	C_J		0.3		pF	VR = 0V, f = 1MHz

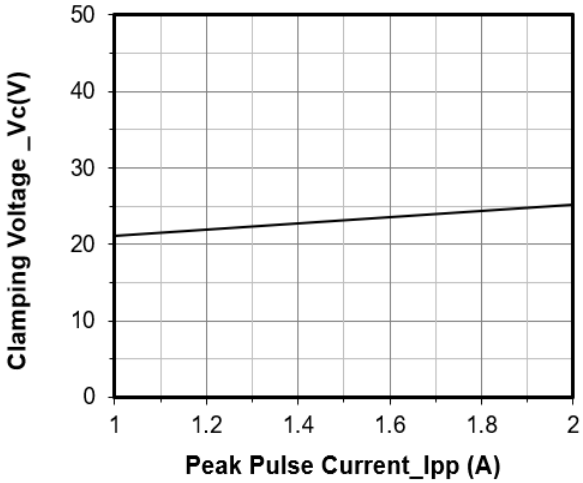
Typical Performance Characteristics (TA=25°C unless otherwise Specified)



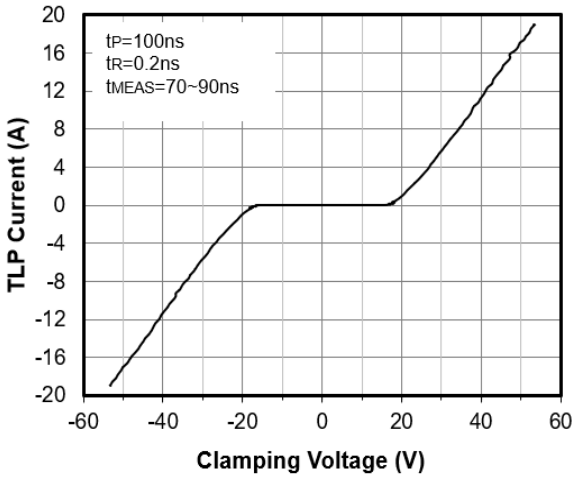
Junction Capacitance vs. Reverse Voltage



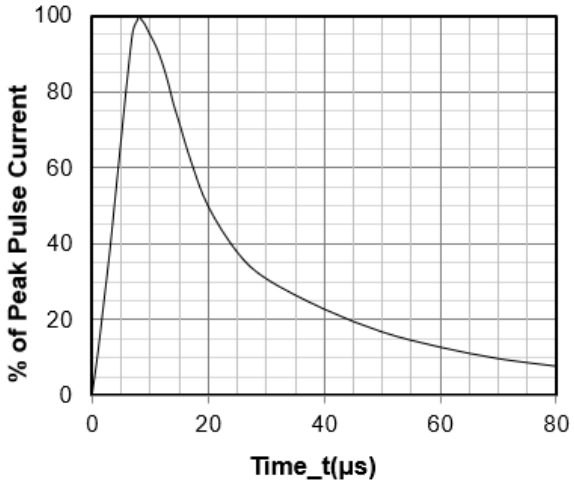
Peak Pulse Power vs. Pulse Time



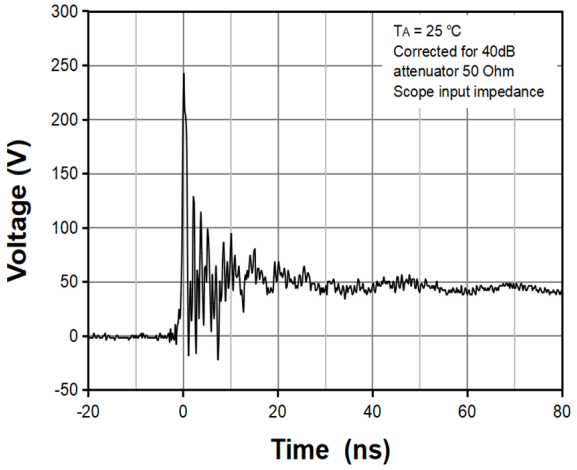
Clamping Voltage vs. Peak Pulse Current (tp = 8/20μs)



TLP Measurement



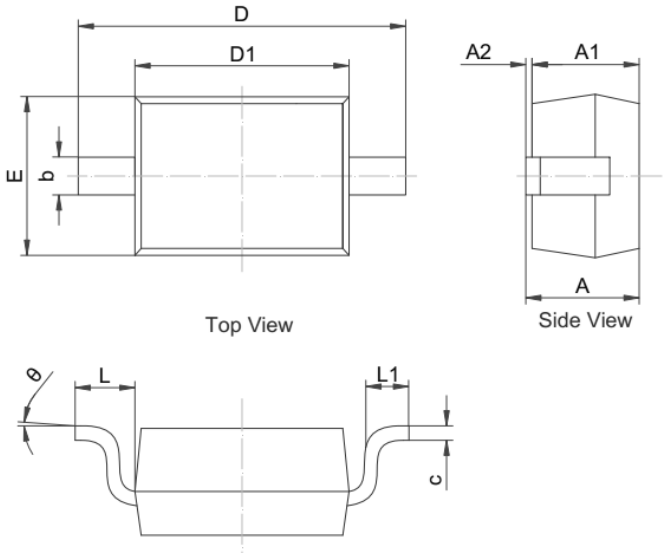
8 X 20μs Pulse Waveform



ESD Clamping Voltage

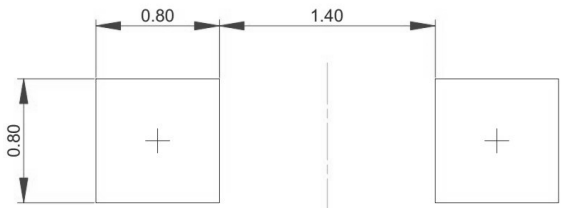
8 kV Contact per IEC61000−4−2

SOD-323 Package Outline Drawing



SYM	MILLIMETERS		
	MIN	NOM	MAX
A	0.800	- -	1.100
A1	0.800	- -	0.900
A2	0.000	- -	0.100
b	0.250	- -	0.400
c	0.080	- -	0.177
D1	1.600	1.700	1.800
D	2.300	- -	2.800
E	1.150	- -	1.400
L	0.475REF		
L1	0.100	- -	0.500
Θ	0°	- -	8°

Suggested Land Pattern



Unit：mm

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